L Number	Hits	Search Text	DB	Time stamp
-	1454	(nmos pmos cmos nfet pfet) and ((gate transistor fet mosfet) with (polysilicon poly polysi) with (oxidation oxidized oxidizing oxidate oxidating oxidize))	USPAT; US-PGPUB	2004/07/08 13:49
-	1533	(nmos pmos cmos nfet pfet) and ((gate transistor fet mosfet) with (polysilicon poly polysi) with (oxidation oxidized oxidizing oxidate oxidating oxidize))	USPAT; US-PGPUB	2004/07/07 11:11
-	3	(nmos pmos cmos nfet pfet) and ((gate transistor fet mosfet) with (polysilicon poly polysi) with (oxidation oxidized oxidizing oxidate oxidating oxidize) with stress$)	USPAT; US-PGPUB	2004/07/08 13:49
-	41	(nmos pmos cmos nfet pfet) and ((gate transistor fet mosfet) same ((polysilicon poly polysi) with (oxidation oxidized oxidizing oxidate oxidating oxidize)) same stress$)	USPAT; US-PGPUB	2004/07/08 13:51
-	2	10/134201	USPAT; US-PGPUB	2004/07/07 17:26
-	1	10/249228	USPAT; US-PGPUB	2004/07/07 17:33
-	3	10/134436	USPAT; US-PGPUB	2004/07/07 18:36
-	67	("6228694"|"6406973"|"6281532"|"5683934"|"6368931"|"5310446"|"4853076"|"009079	USPAT; US-PGPUB	2004/07/07 18:58
-	0	2002/0090791	USPAT; US-PGPUB	2004/07/07 18:58
-	0	2002/0090791	USPAT; US-PGPUB	2004/07/07 18:58
-	1	"20020090791"	USPAT; US-PGPUB	2004/07/07 18:58
-	1	"20020074598"	USPAT; US-PGPUB	2004/07/07 18:59
-	1	"20030040158"	USPAT; US-PGPUB	2004/07/07 18:59
-	1	"20020086472"	USPAT; US-PGPUB	2004/07/07 19:00
-	71	(("6228694"|"6406973"|"6281532"|"5683934"|"6368931"|"5310446"|"4853076"|"00907 or "20020090791" or "20020074598" or "20030040158" or "20020086472"	USPAT; US-PGPUB	2004/07/08 13:46
-	23	((("6228694"|"6406973"|"6281532"|"5683934"|"6368931"|"5310446"|"4853076"|"0090 or "20020090791" or "20020074598" or "20030040158" or "20020086472")	USPAT; US-PGPUB	2004/07/07
-	23	and (("6228694"|"6406973"|"6281532"|"5683934"|"6368931"|"5310446"|"4853076"|"0090 oxidation oxidizing oxidate oxidating oxidize) or "20020090791" or "20020074598" or "20030040158" or "20020086472") and	USPAT; US-PGPUB	2004/07/07
-	28	(("6228694"|"6406973"|"6281532"|"5683934"|"6368931"|"5310446"|"4853076"|"0090 oxidation oxidizing oxidate oxidating oxidize) or "20020090791" or "20020074598" or "20030040158" or "20020086472") and	USPAT; US-PGPUB	2004/07/07
-	17	(("6228694"|"6406973"|"6281532"|"5683934"|"6368931"|"5310446"|"4853076"|"0090 or "20020090791" or "20020074598" or "20030040158" or "20020086472") and ((oxidation oxidized oxidizing oxidate oxidating oxidize) same stress$)) and (	USPAT; US-PGPUB	2004/07/07
-	6	((("6228694"|"6406973"|"6281532"|"5683934"|"6368931"|"5310446"|"4853076"|"0090 or "20020090791" or "20020074598" or "20030040158" or "20020086472") and (oxidation oxidized oxidizing oxidate oxidating oxidize) same stress$)) not ((	USPAT; US-PGPUB	2004/07/07
-	11	((("6228694"|"6406973"|"6281532"|"5683934"|"6368931"|"5310446"|"4853076"|"0090 or "20020090791" or "20020074598" or "20030040158" or "20020086472") and (oxidation oxidized oxidizing oxidate oxidating oxidize) same stress$) and ((("6228694"\|"6406973"\|"6281532"\|"5683934" or "20020090791" or "20020074598" or "20030040158" or "20020086472") and ((oxidation oxidized oxidizing oxidate oxidating oxidize) same stress$)) and (	USPAT; US-PGPUB	2004/07/07

((("6228694"\|"6406973"\|"6281532"\|"5683934"\|"6368931"\|"5310446"\|"4853076"\|"0090 or "20020090791" or "20020074598" or "20030040158" or "20020086472") and

-	71	(("6228694" | "6406973" | "6281532" | "5683934" | "6382931" | "5210044" | "6853076" | "00907 or "20020090791" or "20020074598" or	US-PGPUB	2004/07/08 13:46
-	6	("20020086988" | "6406973" | "6281832" | "5683934" | "6382931" | "5210044" | "6853076" | "0090 or "20020090791" or "20020074598" or	US-PGPUB	2004/07/08 13:46
-	4	("20030080158" | "5683934" | "20020086924" | and 6046098").PN.	USPAT	2004/07/08 13:48
-	1	6362082.URPN.	USPAT	2004/07/08 13:48
-	2	6281532.URPN.	USPAT	2004/07/08 13:49
-	3	(nmos pmos cmos nfet cmosfet pfet nmosfet pmosfet) and ((gate transistor fet mosfet) with (polysilicon poly polysi) with (oxidation oxidized oxidizing oxidate oxidating oxidize) with stress$)	USPAT; US-PGPUB	2004/07/08 13:50
-	41	(nmos pmos cmos nfet pfet cmosfet nmosfet pmosfet) and ((gate transistor fet mosfet) same ((polysilicon poly polysi) with (oxidation oxidized oxidizing oxidate oxidating oxidize)) same stress$)	USPAT; US-PGPUB	2004/07/08 13:50
-	8	(((nmos nfet nmosfet) with tensile) same (oxidation oxidized oxidizing oxidate oxidating oxidize)) and (cmosfet cmos pfet pmos pmosfet)	USPAT; US-PGPUB	2004/07/08 13:57
-	37	(nmos nfet nmosfet) with (oxidation oxidized oxidizing oxidate oxidating oxidize) with (polysilicon poly polysi)	USPAT; US-PGPUB	2004/07/08 13:58
-	35	((nmos nfet nmosfet) with (oxidation oxidized oxidizing oxidate oxidating oxidize) with (polysilicon poly polysi)) and (pmos pmosfet pfet cmos cmosfet)	USPAT; US-PGPUB	2004/07/08 15:02
-	0	((oxidiz$ near2 (nfet nmos nmosfet)) with tensile)	USPAT; US-PGPUB	2004/07/08 15:03
-	0	((oxidat$ near2 (nfet nmos nmosfet)) with tensile)	USPAT; US-PGPUB	2004/07/08 15:03
-	1	((oxide near2 (nfet nmos nmosfet)) with tensile)	USPAT; US-PGPUB	2004/07/08 15:03
-	0	((oxidiz$ with (nfet nmos nmosfet)) with tensile)	USPAT; US-PGPUB	2004/07/08 15:05
-	2	((oxidat$ with (nfet nmos nmosfet)) with tensile)	USPAT; US-PGPUB	2004/07/08 15:04
-	0	((oxidat$ with (nfet nmos nmosfet)) with tensile)	EPO; JPO; DERWENT; IBM_TDB	2004/07/08 15:04
-	0	((oxidiz$ with (nfet nmos nmosfet)) with tensile)	EPO; JPO; DERWENT; IBM_TDB	2004/07/08 15:05
-	1713	((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.	USPAT; US-PGPUB	2004/07/08 15:08
-	346	(438/279).CCLS.	USPAT; US-PGPUB	2004/07/08 15:08
-	2024	(((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)	USPAT; US-PGPUB	2004/07/08 15:09
-	1352	((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)	USPAT; US-PGPUB	2004/07/08 15:10
-	159	(((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and (stress$ tensile compressive)	USPAT; US-PGPUB	2004/07/08 15:16
-	159	((((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and (stress$ tensile compressive)) not (@ad>20030923 or @rlad>20030923)	USPAT; US-PGPUB	2004/07/08 15:14

-	1243	(((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and ((oxidiz$ oxidat$ oxide) with (gate transistor fet mosfet nfet nmosfet))	USPAT; US-PGPUB	2004/07/08 15:16
-	572	(((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and ((oxidiz$ oxidat$) with (gate transistor fet mosfet nfet nmosfet))	USPAT; US-PGPUB	2004/07/08 15:17
-	80	(((((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and (stress$ tensile compressive)) not (@ad>20030923 or @rlad>20030923)) and ((((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and ((oxidiz$ oxidat$) with (gate transistor fet mosfet nfet nmosfet)))	USPAT; US-PGPUB	2004/07/08 15:17
-	78	((((((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and (stress$ tensile compressive)) not (@ad>20030923 or @rlad>20030923)) and ((((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and ((oxidiz$ oxidat$) with (gate transistor fet mosfet nfet nmosfet)))) not ((nmos pmos cmos nfet pfet cmosfet nmosfet pmosfet) and ((gate transistor fet mosfet) same ((polysilicon poly polysi) with (oxidation oxidized oxidizing oxidate oxidating oxidize)) same stress$))	USPAT; US-PGPUB	2004/07/08 15:46
-	76828	cmos Cmosfet	USPAT; US-PGPUB	2004/07/08 15:47
-	2407	(cmos Cmosfet) and (mask with (nitride and (PR photoresist)))	USPAT; US-PGPUB	2004/07/08 15:56
-	182	(cmos Cmosfet) and (mask with (nitride near2 (PR photoresist)))	USPAT; US-PGPUB	2004/07/08 15:56
-	91	(cmos Cmosfet) and (mask near2 (nitride near2 (PR photoresist)))	USPAT; US-PGPUB	2004/07/08 15:56
-	0	(cmos Cmosfet) and (mask near2 (nitride near2 (PR photoresist)) with "or")	USPAT; US-PGPUB	2004/07/08 15:56
-	0	(cmos Cmosfet) and (mask with (nitride near2 (PR photoresist))with "or")	USPAT; US-PGPUB	2004/07/08 15:56
-	0	(cmos Cmosfet) and (mask with (nitride and (PR photoresist))with "or")	USPAT; US-PGPUB	2004/07/08 16:06
-	0	(cmos Cmosfet) and ((silicide or salicide) with (remove with unreacted) with (nfet nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 16:07
-	0	(cmos Cmosfet) and ((silicide or salicide) with (remove with unreacted) same (nfet nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 16:07
-	146	(cmos Cmosfet) and ((silicide or salicide) with (remove with unreacted))	USPAT; US-PGPUB	2004/07/08 17:18
-	6	(cmos Cmosfet) and ((silicide or salicide) with (remove) with (NFET nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 17:18
-	5	(cmos Cmosfet) and ((silicide Cosi tisi wsi mosi) with (remove) with (NFET nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 17:10

–	0	((cmos Cmosfet) and ((silicide Cosi tisi wsi mosi) with (remove) with (NFET nmos nmosfet))) not ((cmos Cmosfet) and ((silicide or salicide) with (remove) with (NFET nmos nmosfet)))	USPAT; US-PGPUB	2004/07/08 17:10
–	226	(jennifer near2 kennedy).xa.	USPAT; US-PGPUB	2004/07/08 17:14
–	77	((jennifer near2 kennedy).xa.) and silicide	USPAT; US-PGPUB	2004/07/08 17:14
–	14	((jennifer near2 kennedy).xa.) and ((silicide salicide cosi wsi tisi) with remov$)	USPAT; US-PGPUB	2004/07/08 17:15
–	595	(cmos Cmosfet) and ((silicide or salicide) with (remov$ with unreacted))	USPAT; US-PGPUB	2004/07/08 17:18
–	449	((cmos Cmosfet) and ((silicide or salicide) with (remov$ with unreacted))) not ((cmos Cmosfet) and ((silicide or salicide) with (remove with unreacted)))	USPAT; US-PGPUB	2004/07/08 17:18
–	21	(cmos Cmosfet) and ((silicide or salicide) with (remov$) with (NFET nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 17:27
–	21	(cmos Cmosfet) and ((silicide or salicide cosi mosi tisi wsi) with (remov$) with (NFET nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 17:28
–	0	(cmos Cmosfet) and ((silicide or salicide cosi mosi tisi wsi) with (remov$ etching etched etch) with (NFET nmos nmosfet) with top)	USPAT; US-PGPUB	2004/07/08 17:28
–	126	(cmos Cmosfet) and ((silicide or salicide cosi mosi tisi wsi) with (remov$ etching etched etch) with (NFET nmos nmosfet gate transistor fet) with top)	USPAT; US-PGPUB	2004/07/08 17:29
–	126	(cmos Cmosfet) and ((silicide or salicide cosi mosi tisi wsi) with (remov$ etching etched etch) with (NFET nmos nmosfet gate transistor fet mosfet) with top)	USPAT; US-PGPUB	2004/07/08 17:30
–	19	(cmos Cmosfet) and ((silicide or salicide cosi mosi tisi wsi) with ((remov$ etching etched etch) near2 top) with (NFET nmos nmosfet gate transistor fet mosfet))	USPAT; US-PGPUB	2004/07/08 19:07
–	19	"5828131"	USPAT; US-PGPUB	2004/07/08 19:08
–	1	("5828131").PN.	USPAT; US-PGPUB	2004/07/08 19:07
–	1	"20020031909"	USPAT; US-PGPUB	2004/07/08 19:09
–	0	"200400087160"	USPAT; US-PGPUB	2004/07/08 19:09
–	1	"20040087160"	USPAT; US-PGPUB	2004/07/08 19:09